



IMPORTANT NOTICE

10 December 2015

1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

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Thank you for your cooperation and understanding,

WeEn Semiconductors



1. General description

AC Thyristor power switch in a SOT54 plastic package with self-protective capabilities against low and high energy transients

2. Features and benefits

- Exclusive negative gate triggering
- Full cycle AC conduction
- High noise immunity
- Remote gate separates the gate driver from the effects of the load current
- Very sensitive gate for lowest gate trigger current
- Safe clamping of low energy over-voltage transients
- Self-protective turn-on during high energy voltage transients

3. Applications

- Fan motor circuits
- Pump motor circuits
- Lower-power highly inductive, resistive and safety loads

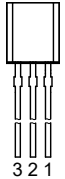
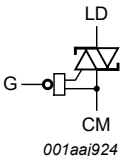
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{lead} \leq 71 \text{ }^\circ\text{C}$; Fig. 1	-	-	0.8	A
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12 \text{ V}$; $I_T = 100 \text{ mA}$; LD+ G-; $T_j = 25 \text{ }^\circ\text{C}$; Fig. 6	0.5	-	5	mA
		$V_D = 12 \text{ V}$; $I_T = 100 \text{ mA}$; LD- G-; $T_j = 25 \text{ }^\circ\text{C}$; Fig. 6	0.5	-	5	mA

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	CM	common	 <p>TO-92 (SOT54)</p>	 <p>001aa 924</p>
2	G	gate		
3	LD	load		

6. Ordering information

Table 3. Ordering information

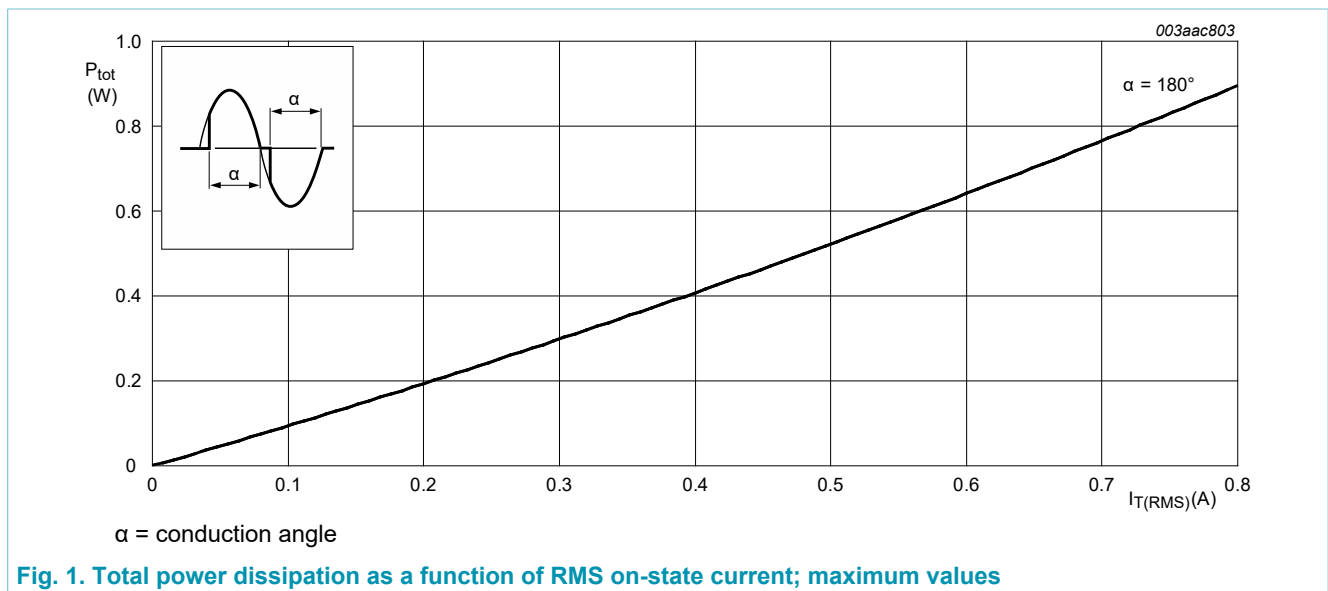
Type number	Package		
	Name	Description	Version
ACT108-600D	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54
ACT108-600D/DG	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{lead} \leq 71\text{ °C}$; Fig. 1	-	0.8	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$	-	8.8	A
		full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig. 2 ; Fig. 3	-	8	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; SIN	-	0.32	A ² s
di_T/dt	rate of rise of on-state current	$I_G = 10\text{ mA}$	-	50	A/ μ s
I_{GM}	peak gate current	$t = 20\text{ }\mu$ s	-	1	A
V_{GM}	peak gate voltage		-	15	V
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.1	W
T_{stg}	storage temperature		-40	150	°C
T_j	junction temperature		-	125	°C
V_{PP}	peak pulse voltage	$T_j = 25\text{ °C}$; non-repetitive, off-state; Fig. 4	-	2	kV



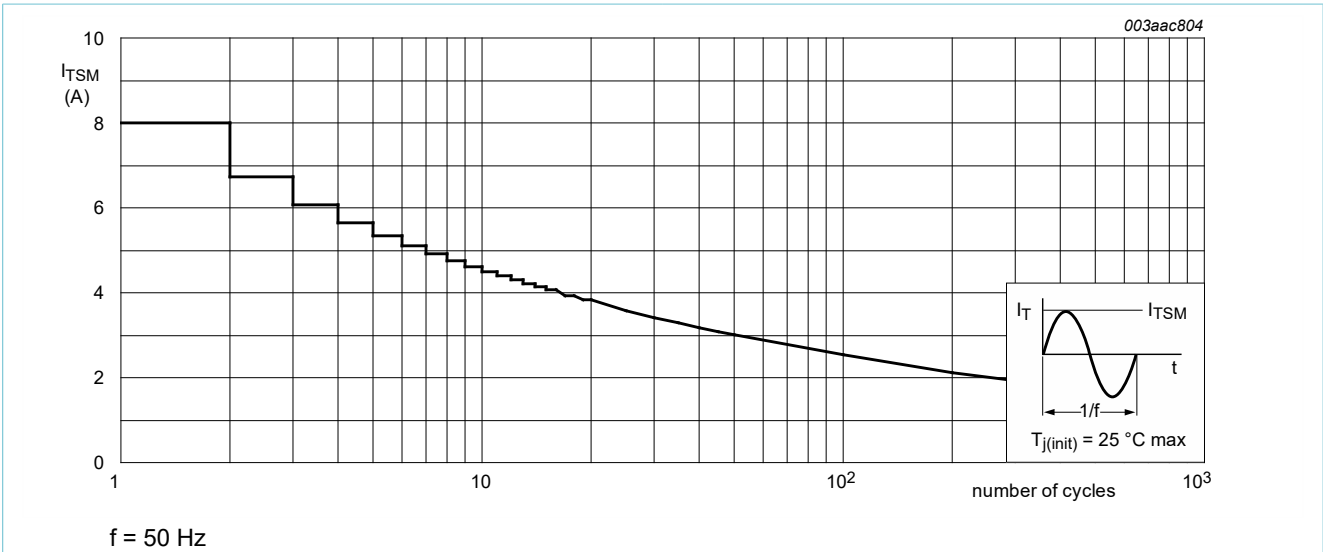


Fig. 2. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

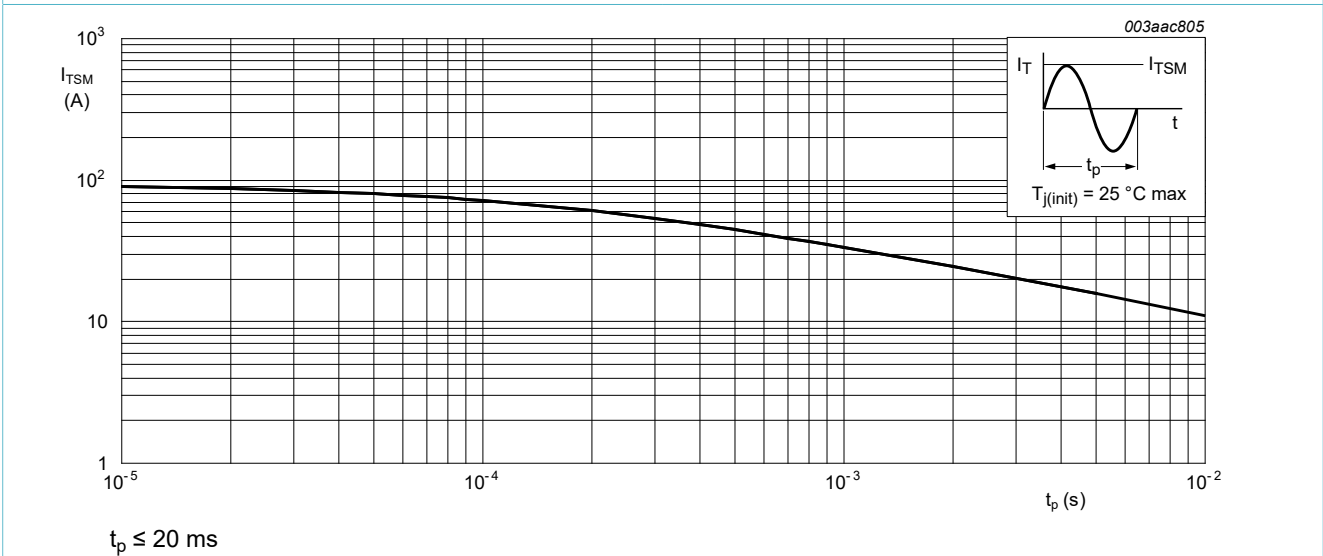


Fig. 3. Non-repetitive peak on-state current as a function of pulse width; maximum values

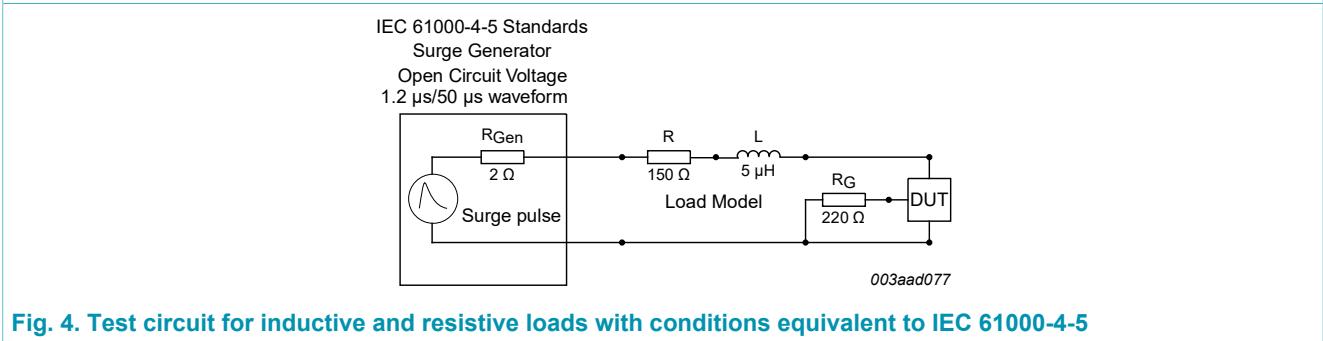


Fig. 4. Test circuit for inductive and resistive loads with conditions equivalent to IEC 61000-4-5

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	full cycle with heatsink compound; Fig. 5	-	-	60	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	full cycle; printed-circuit board mounted; lead length 4 mm	-	150	-	K/W

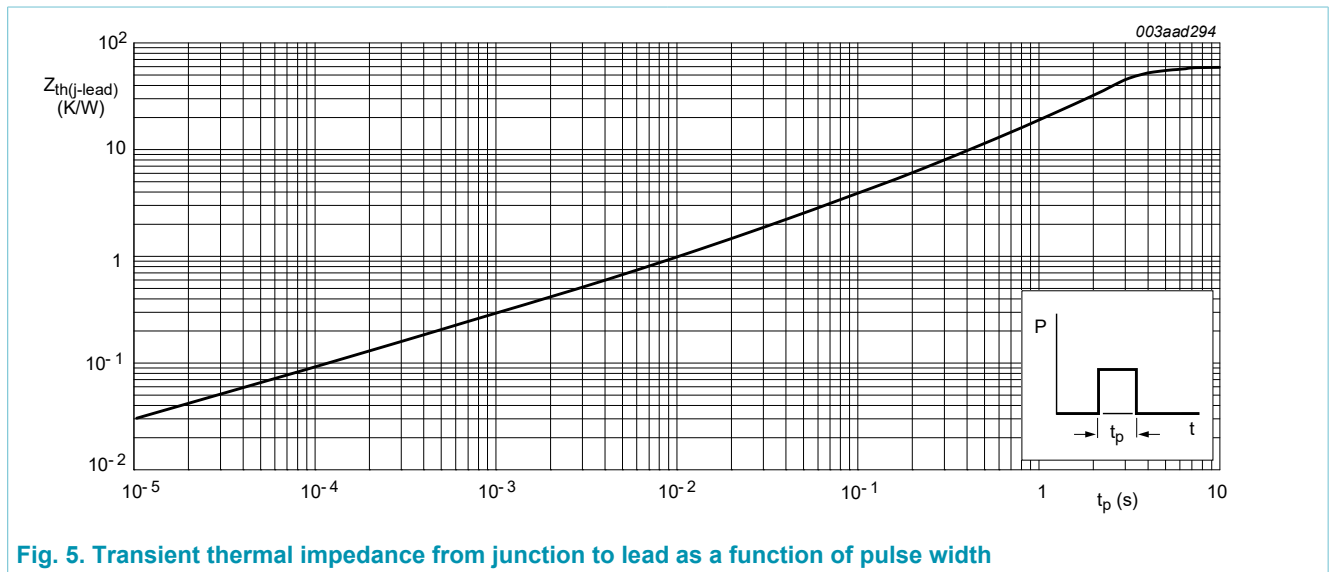
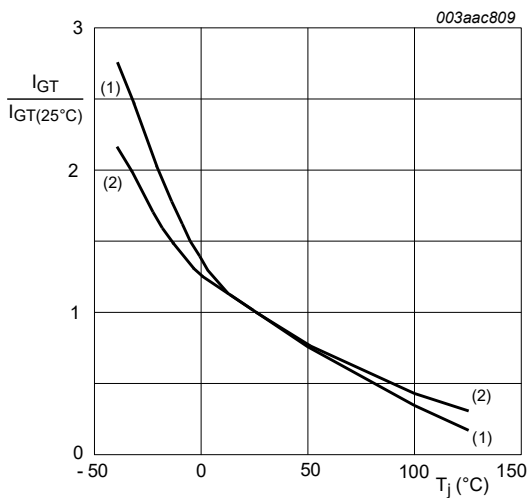


Fig. 5. Transient thermal impedance from junction to lead as a function of pulse width

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I _{GT}	gate trigger current	V _D = 12 V; I _T = 100 mA; LD+ G-; T _j = 25 °C; Fig. 6	0.5	-	5	mA
		V _D = 12 V; I _T = 100 mA; LD- G-; T _j = 25 °C; Fig. 6	0.5	-	5	mA
I _L	latching current	V _D = 12 V; I _G = 100 mA; LD+ G-; T _j = 25 °C; Fig. 7	-	-	25	mA
		V _D = 12 V; I _G = 100 mA; LD- G-; T _j = 25 °C; Fig. 7	-	-	25	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; Fig. 8	-	-	20	mA
V _T	on-state voltage	I _T = 1.1 A; T _j = 25 °C; Fig. 9	-	-	1.3	V
V _{GT}	gate trigger voltage	V _D = 400 V; I _T = 100 mA; T _j = 125 °C	0.15	-	-	V
		V _D = 12 V; I _T = 100 mA; T _j = 25 °C	-	-	0.9	V
I _D	off-state current	V _D = 600 V; T _j = 25 °C	-	-	2	µA
		V _D = 600 V; T _j = 125 °C	-	-	0.2	mA
V _{CL}	clamping voltage	I _{CL} = 0.1 mA; t _p = 1 ms; T _j ≤ 125 °C	650	-	-	V
Dynamic characteristics						
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 402 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit; Fig. 10	300	-	-	V/µs
di _{com} /dt	rate of change of commutating current	V _D = 400 V; T _j = 125 °C; I _{T(RMS)} = 1 A; dV _{com} /dt = 15 V/µs; gate open circuit; Fig. 11 ; Fig. 12	0.15	-	-	A/ms



(1) LD+ G-
(2) LD- G-

Fig. 6. Normalized gate trigger current as a function of junction temperature

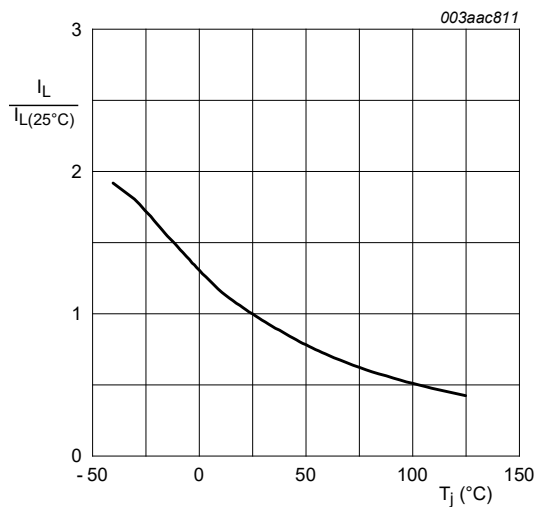


Fig. 7. Normalized latching current as a function of junction temperature

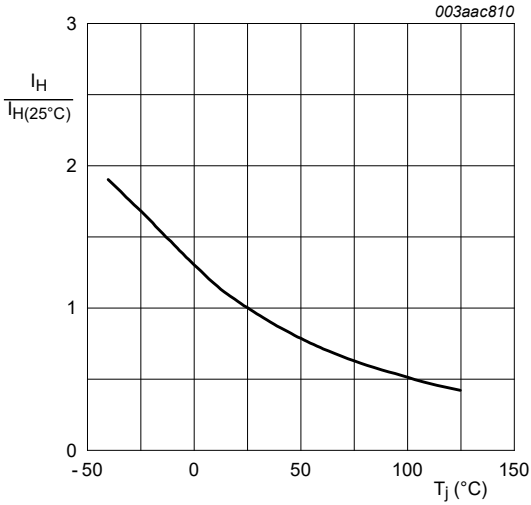
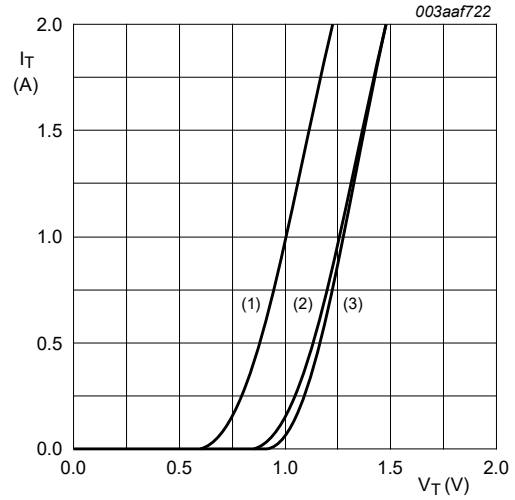


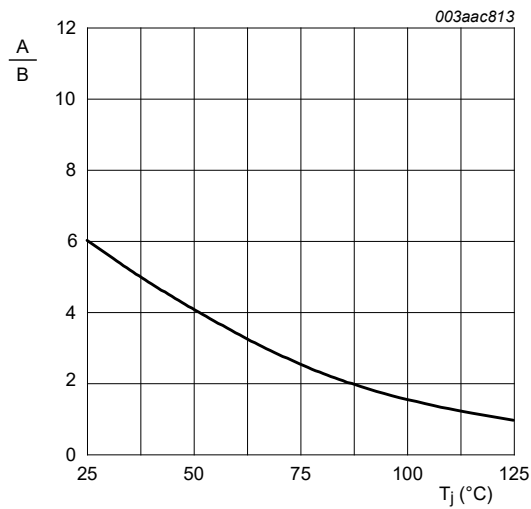
Fig. 8. Normalized holding current as a function of junction temperature



$V_o = 0.758 \text{ V}; R_s = 0.263 \Omega$

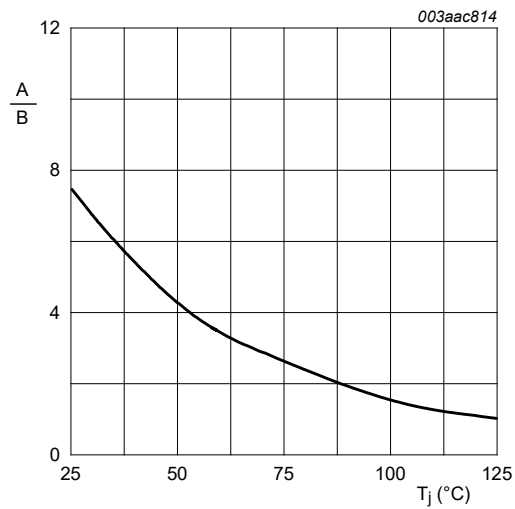
- (1) $T_j = 125 \text{ }^\circ\text{C}$; typical values
- (2) $T_j = 125 \text{ }^\circ\text{C}$; maximum values
- (3) $T_j = 25 \text{ }^\circ\text{C}$; maximum values

Fig. 9. On-state current as a function of on-state voltage



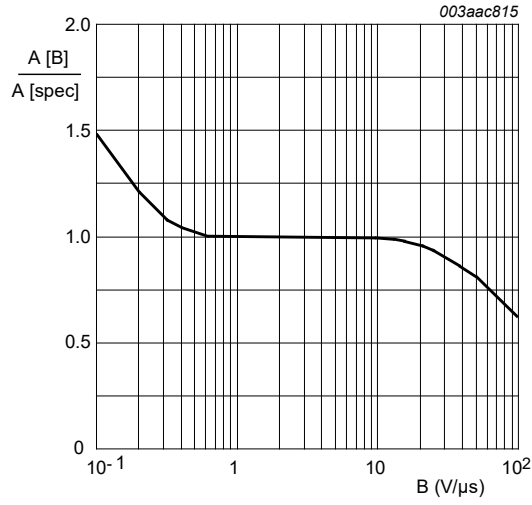
$A = dV_D/dt$ at condition $T_j \text{ }^\circ\text{C}$
 $B = dV_D/dt$ at condition $T_j [125] \text{ }^\circ\text{C}$

Fig. 10. Normalized rate of rise of off-state voltage as a function of junction temperature



$A = di_{com}/dt$ at condition $T_j \text{ }^\circ\text{C}$
 $B = di_{com}/dt$ at condition $T_j [125] \text{ }^\circ\text{C}$
 $V_D = 400 \text{ V}$

Fig. 11. Normalized critical rate of rise of commutating current as a function of junction temperature



A [B] = dl_{com}/dt at condition B, dV_{com}/dt
 A [spec] is the data sheet value for dl_{com}/dt
 turn-off time is less than 20 ms

Fig. 12. Normalized critical rate of change of commutating current as a function of critical rate of change of commutating voltage; minimum values

10. Package outline



Fig. 13. Package outline TO-92 (SOT54)

11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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Date of release: 22 September 2016